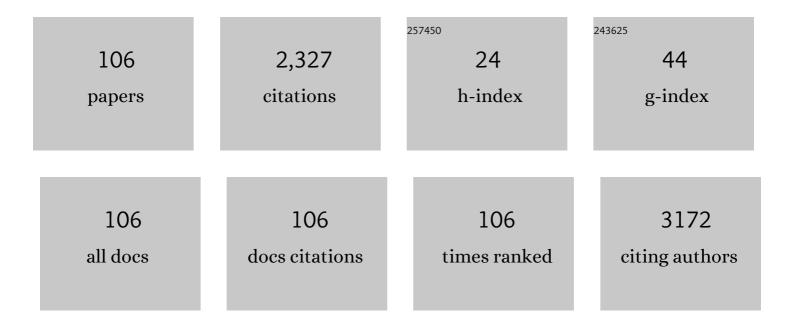
List of Publications by Year in descending order

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Ονίδο Βρατινία

| # | Article | IF | CITATIONS |
|----|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|-----------|
| 1 | Flexible non-volatile optical memory thin-film transistor device with over 256 distinct levels based on an organic bicomponent blend. Nature Nanotechnology, 2016, 11, 769-775. | 31.5 | 300 |
| 2 | Optically switchable transistor via energy-level phototuning in a bicomponent organic semiconductor. Nature Chemistry, 2012, 4, 675-679. | 13.6 | 217 |
| 3 | Local interface composition and band discontinuities in heterovalent heterostructures. Physical Review Letters, 1994, 72, 294-297. | 7.8 | 130 |
| 4 | Tuning AlAs-GaAs band discontinuities and the role of Si-induced local interface dipoles. Physical Review B, 1991, 43, 2450-2453. | 3.2 | 123 |
| 5 | The effect of polymer molecular weight on the performance of PTB7-Th:O-IDTBR non-fullerene organic solar cells. Journal of Materials Chemistry A, 2018, 6, 9506-9516. | 10.3 | 76 |
| 6 | A nanomesh scaffold for supramolecular nanowire optoelectronic devices. Nature Nanotechnology, 2016, 11, 900-906. | 31.5 | 72 |
| 7 | Highly active photocatalytic coatings prepared by a low-temperature method. Environmental Science and Pollution Research, 2014, 21, 11238-11249. | 5.3 | 58 |
| 8 | Microscopic capacitors and neutral interfaces in III-V/IV/III-V semiconductor heterostructures. Physical Review Letters, 1992, 69, 1283-1286. | 7.8 | 52 |
| 9 | Multiresponsive Nonvolatile Memories Based on Optically Switchable Ferroelectric Organic Fieldâ€Effect Transistors. Advanced Materials, 2021, 33, e2007965. | 21.0 | 52 |
| 10 | AlAs-GaAs heterojunction engineering by means of group-IV elemental interface layers. Physical Review B, 1992, 45, 4528-4531. | 3.2 | 45 |
| 11 | Photo-induced intramolecular charge transfer in an ambipolar field-effect transistor based on a π-conjugated donor–acceptor dyad. Journal of Materials Chemistry C, 2013, 1, 3985. | 5.5 | 45 |
| 12 | Structure and local dipole of Si interface layers in AlAs-GaAs heterostructures. Physical Review B, 1992, 46, 6834-6845. | 3.2 | 44 |
| 13 | Growth of ultrathin pentacene films on polymeric substrates. Physical Review B, 2009, 80, . | 3.2 | 40 |
| 14 | Behavior of the (0001) surface of sapphire upon high-temperature annealing. Surface Science, 2007, 601, 44-49. | 1.9 | 37 |
| 15 | Influence of transfer residue on the optical properties of chemical vapor deposited graphene investigated through spectroscopic ellipsometry. Journal of Applied Physics, 2013, 114, . | 2.5 | 37 |
| 16 | Electron-Withdrawing Substituted Tetrathiafulvalenes as Ambipolar Semiconductors. Chemistry of Materials, 2011, 23, 851-861. | 6.7 | 32 |
| 17 | Self‣uspended Nanomesh Scaffold for Ultrafast Flexible Photodetectors Based on Organic Semiconducting Crystals. Advanced Materials, 2018, 30, e1801181. | 21.0 | 32 |
| 18 | Lack of band-offset transitivity for semiconductor heterojunctions with polar orientation: ZnSe-Ge(001), Ge-GaAs(001), and ZnSe-GaAs(001). Physical Review B, 1994, 50, 11723-11729. | 3.2 | 31 |

| # | Article | IF | CITATIONS |
|----|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|-----------|
| 19 | Epitaxial growth and interface parameters of Si layers on GaAs(001) and AlAs(001) substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2225. | 1.6 | 30 |
| 20 | Microscopic control of ZnSe-GaAs heterojunction band offsets. Physica B: Condensed Matter, 1993, 185, 557-565. | 2.7 | 30 |
| 21 | ZnSe-GaAs heterojunction parameters. Journal of Crystal Growth, 1993, 127, 387-391. | 1.5 | 29 |
| 22 | Band offsets and strain in CdTe-GaAs heterostructures. Physical Review B, 1993, 48, 8899-8910. | 3.2 | 26 |
| 23 | Novel Chitosan–Mg(OH) ₂ -Based Nanocomposite Membranes for Direct Alkaline Ethanol Fuel Cells. ACS Sustainable Chemistry and Engineering, 2019, 7, 19356-19368. | 6.7 | 26 |
| 24 | Time-of-flight mobility of charge carriers in position-dependent electric field between coplanar electrodes. Applied Physics Letters, 2012, 101, 093304. | 3.3 | 25 |
| 25 | Pentacene on graphene: Differences between single layer and bilayer. Carbon, 2014, 69, 162-168. | 10.3 | 23 |
| 26 | Influence of Solid-State Microstructure on the Electronic Performance of 5,11-Bis(triethylsilylethynyl) Anthradithiophene. Chemistry of Materials, 2013, 25, 1823-1828. | 6.7 | 21 |
| 27 | Fastâ€Response Photonic Device Based on Organicâ€Crystal Heterojunctions Assembled into a Vertical‥etâ€Open Asymmetric Architecture. Advanced Materials, 2017, 29, 1605760. | 21.0 | 21 |
| 28 | Arsenic cap layer desorption and the formation of GaAs(001)c(4×4) surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2041. | 1.6 | 20 |
| 29 | In diffusion and electronic energy structure in polymer layers on In tin oxide. Thin Solid Films, 2011, 519, 4216-4219. | 1.8 | 20 |
| 30 | The coherency loss microstructure at a CdTe/GaAs(001) interface. Philosophical Magazine Letters, 1993, 67, 279-285. | 1.2 | 19 |
| 31 | Modification of Al/GaAs(001) Schottky barriers by means of heterovalent interface layers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 2653. | 1.6 | 19 |
| 32 | Atomic scale roughness of GaAs(001)2×4 surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 623. | 1.6 | 19 |
| 33 | Electronic and structural characterisation of a tetrathiafulvalene compound as a potential candidate for ambipolar transport properties. CrystEngComm, 2011, 13, 6597. | 2.6 | 19 |
| 34 | Mo6S9â^'xIx nanowires as additives for enhanced organic solar cell performance. Solar Energy Materials and Solar Cells, 2014, 127, 63-66. | 6.2 | 19 |
| 35 | Solution-Processed Graphene–Nanographene van der Waals Heterostructures for Photodetectors with Efficient and Ultralong Charge Separation. Journal of the American Chemical Society, 2021, 143, 17109-17116. | 13.7 | 19 |
| 36 | Effect of Water Layer at the SiO ₂ /Graphene Interface on Pentacene Morphology. Langmuir, 2014, 30, 11681-11688. | 3.5 | 18 |

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| 37 | Modulation of charge transport properties of reduced graphene oxide by submonolayer physisorption of an organic dye. Organic Electronics, 2013, 14, 1787-1792. | 2.6 | 17 |
| 38 | Contact resistance in organic thin film transistors. Synthetic Metals, 2009, 159, 1210-1214. | 3.9 | 16 |
| 39 | Single-step solution processing of small-molecule organic semiconductor field-effect transistors at high yield. Applied Physics Letters, 2011, 99, . | 3.3 | 16 |
| 40 | Graphene-Induced Enhancement of n-Type Mobility in Perylenediimide Thin Films. Journal of Physical Chemistry C, 2014, 118, 24819-24826. | 3.1 | 16 |
| 41 | Factors determining large observed increases in power conversion efficiency of P3HT:PCBM solar cells embedded with Mo6S9â^'xlx nanowires. Synthetic Metals, 2016, 212, 105-112. | 3.9 | 16 |
| 42 | Fabrication of poly(3-hexylthiophene) nanowires for high-mobility transistors. Organic Electronics, 2016, 30, 92-98. | 2.6 | 16 |
| 43 | Characterization of Pure and Modified TiO \$\$_{2}\$\$ 2 Layer on Glass and Aluminum Support by Beam Deflection Spectrometry. International Journal of Thermophysics, 2014, 35, 1990-2000. | 2.1 | 14 |
| 44 | Tuning AlAs-GaAs heterostructure properties by means of MBE-grown Si interface layers. Surface Science, 1991, 251-252, 82-86. | 1.9 | 13 |
| 45 | Phonons in Si/GaAs superlattices. Physical Review B, 1992, 46, 7296-7299. | 3.2 | 13 |
| 46 | Engineering ZnSe-GaAs band offsets. Journal of Crystal Growth, 1992, 117, 573-577. | 1.5 | 13 |
| 47 | Modification of heterojunction band offsets at III–V/IV/III–V interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1628. | 1.6 | 13 |
| 48 | Structural properties of heterostructures with engineered band offsets. Journal of Crystal Growth, 1996, 159, 703-708. | 1.5 | 13 |
| 49 | Characterisation of charge carrier transport in thin organic semiconductor layers by time-of-flight photocurrent measurements. Organic Electronics, 2019, 64, 117-130. | 2.6 | 13 |
| 50 | Si-GaAs(001) superlattice structure. Journal of Crystal Growth, 1993, 127, 121-125. | 1.5 | 12 |
| 51 | Displacement current in bottom-contact organic thin-film transistor. Journal Physics D: Applied Physics, 2008, 41, 135109. | 2.8 | 12 |
| 52 | Grafold-driven nucleation of pentacene on graphene. Surface Science, 2013, 609, L5-L8. | 1.9 | 12 |
| 53 | Influence of a gold substrate on the optical properties of graphene. Journal of Applied Physics, 2015, 117, . | 2.5 | 12 |
| 54 | Chemical vapor deposition of Al from dimethylethylamine alane on GaAs(100)c(4×4) surfaces. Journal of Applied Physics, 1994, 76, 3471-3478. | 2.5 | 11 |

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| 55 | Initial stages of growth of organic semiconductors on vicinal (0001) sapphire surfaces. Surface Science, 2008, 602, 1368-1375. | 1.9 | 11 |
| 56 | Ionization Energy and Energy Gap Structure of MoSI Molecular Wires: Kelvin Probe, Ultraviolet Photoelectron Spectroscopy, and Cyclic Voltammetry Measurements. Langmuir, 2011, 27, 4296-4299. | 3.5 | 11 |
| 57 | Charge carrier transport in polycrystalline CH3NH3PbI3 perovskite thin films in a lateral direction characterized by time-of-flight photoconductivity. Materials Chemistry and Physics, 2018, 220, 182-189. | 4.0 | 11 |
| 58 | Elucidation of Donor:Acceptor Phase Separation in Nonfullerene Organic Solar Cells and Its Implications on Device Performance and Charge Carrier Mobility. ACS Applied Energy Materials, 2019, 2, 7535-7545. | 5.1 | 11 |
| 59 | Conjugated Polymer Mesocrystals with Structural and Optoelectronic Coherence and Anisotropy in Three Dimensions. Advanced Materials, 2022, 34, e2103002. | 21.0 | 11 |
| 60 | Siâ€GaAs(001) superlattices. Applied Physics Letters, 1992, 61, 1570-1572. | 3.3 | 10 |
| 61 | Chemical bonding and electronic properties of Seâ€rich ZnSe–GaAs(001) interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 3135-3143. | 2.1 | 10 |
| 62 | Al/ZnSe(100) Schottky-barrier height versus initial ZnSe surface reconstruction. Physical Review B, 1998, 57, R9431-R9434. | 3.2 | 10 |
| 63 | Graphene flakes at the SiO2/organic-semiconductor interface for high-mobility field-effect transistors. Organic Electronics, 2015, 27, 221-226. | 2.6 | 10 |
| 64 | Cross-sectional lateral-force microscopy of semiconductor heterostructures and multiple quantum wells. Physical Review B, 1995, 52, R8625-R8628. | 3.2 | 9 |
| 65 | Interfacial chemical bonds, reactions, and band alignment in ZnSe/GaAs(001) heterojunctions. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2967. | 1.6 | 9 |
| 66 | Ripening of Rubrene Islands. Journal of Physical Chemistry C, 2007, 111, 18558-18562. | 3.1 | 9 |
| 67 | Low resistance graded contacts to nâ€ŧype ZnSe. Applied Physics Letters, 1996, 68, 370-372. | 3.3 | 8 |
| 68 | Interface resistivity and lifetime of thin film transistors exposed to ambient air. Applied Physics Letters, 2009, 94, 123301. | 3.3 | 8 |
| 69 | Role of transport band edge variation on delocalized charge transport in high-mobility crystalline organic semiconductors. Physical Review B, 2017, 96, . | 3.2 | 8 |
| 70 | Influence of substrate morphology on growth mode of thin organic films: An atomic force microscopy study. Journal of Vacuum Science & Technology B, 2007, 25, 1152. | 1.3 | 7 |
| 71 | Fabrication of rubrene nanowires on vicinal (0001) sapphire surfaces. Surface Science, 2007, 601, L25-L28. | 1.9 | 7 |
| 72 | Interface-controlled growth of organic semiconductors on graphene. Surface Science, 2017, 664, 16-20. | 1.9 | 7 |

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| 73 | Charged versus neutral interfaces in III–V/Ge quantum wells. Journal of Crystal Growth, 1993, 127, 93-97. | 1.5 | 6 |
| 74 | Influence of growth parameters on the properties of ZnSe-GaAs(001) heterostructures. Journal of Crystal Growth, 1995, 150, 765-769. | 1.5 | 6 |
| 75 | Electrical conductivity in metal/3,4,9,10-perylenetetracarboxylic dianhydride/metal structures. Journal of Applied Physics, 2003, 93, 6090-6094. | 2.5 | 6 |
| 76 | Morphology and electronic structure of thin 3,4,9,10-perylenetetracarboxylic dianhydride layers on Si(001). Thin Solid Films, 2006, 515, 1424-1428. | 1.8 | 6 |
| 77 | The role of local potential minima on charge transport in thin organic semiconductor layers. Organic Electronics, 2017, 42, 221-227. | 2.6 | 5 |
| 78 | Evidence of enhanced photocurrent response in corannulene films. RSC Advances, 2017, 7, 45601-45606. | 3.6 | 5 |
| 79 | Negative field-dependent charge mobility in crystalline organic semiconductors with delocalized transport. Chemical Papers, 2018, 72, 1685-1695. | 2.2 | 5 |
| 80 | Some properties of melt-produced YBaCuO wire. Superconductor Science and Technology, 1988, 1, 141-144. | 3.5 | 4 |
| 81 | The role of space-charge-induced electric field on transient photocurrent response in organic semiconductors. Physica Status Solidi (B): Basic Research, 2006, 243, 473-482. | 1.5 | 4 |
| 82 | The role of Ti adhesion layer in electric charge transport in pentacene organic thin film transistors. European Physical Journal B, 2010, 73, 341-346. | 1.5 | 4 |
| 83 | X-ray absorption of cadmium in theL-edge region. Physical Review A, 2011, 84, . | 2.5 | 4 |
| 84 | Morphology of the Metal-organic Semiconductor Contacts: the Role of Substrate Surface Treatment. Springer Proceedings in Physics, 2009, , 205-210. | 0.2 | 3 |
| 85 | Enhancement of Charge Transport in Polythiophene Semiconducting Polymer by Blending with Graphene Nanoparticles. ChemPlusChem, 2019, 84, 1366-1374. | 2.8 | 3 |
| 86 | The role of charge transfer at reduced graphene oxide/organic semiconductor interface on the charge transport properties. Organic Electronics, 2020, 77, 105499. | 2.6 | 3 |
| 87 | Molecular alignment on graphene surface determines transport properties of graphene/organic semiconductor transistors. Organic Electronics, 2020, 87, 105933. | 2.6 | 3 |
| 88 | A pyrrolopyridazinedione-based copolymer for fullerene-free organic solar cells. New Journal of Chemistry, 2021, 45, 1001-1009. | 2.8 | 3 |
| 89 | Vibrational properties of Si/GaAs superlattices. Superlattices and Microstructures, 1992, 12, 429-432. | 3.1 | 2 |
| 90 | Local Interface Composition and Band Offset Tuning in ZnSe-GaAs(001) Heterostructures. Materials Research Society Symposia Proceedings, 1993, 326, 3. | 0.1 | 2 |

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| 91 | <title>Interfacial engineering in blue laser structures</title> . , 1994, 2346, 100. | | 2 |
| 92 | <title>Nanosize stress concentrators at facets in Zn1-xCdxSe/ZnSe multiple quantum well laser structures</title> . , 1994, , . | | 2 |
| 93 | Defect structure at a interface. Thin Solid Films, 1995, 271, 117-121. | 1.8 | 2 |
| 94 | Improved contact resistance to n-type wide gap ll–VI semiconductors. Journal of Crystal Growth, 1996, 159, 718-722. | 1.5 | 2 |
| 95 | Electronic transport in perylenetetracarboxylic dianhydride: The role of In diffusion. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 797-801. | 2.1 | 2 |
| 96 | Enhanced photoconductivity of semiconductor polymers using graphene nanoflakes. Materials Today: Proceedings, 2019, 19, 2591-2595. | 1.8 | 1 |
| 97 | Microstructural and Surface Effects on Fatigue of Ti-6Al-4V Alloy. , 1990, , 344-353. | | 1 |
| 98 | AlAs-GaAs Beterojunction Engineering by Means of Group IV Interface Layers. Materials Research Society Symposia Proceedings, 1991, 240, 603. | 0.1 | 0 |
| 99 | Modification of heterojunction band offsets at III-V/IV/III-V interfaces. , 1993, , . | | Ο |
| 100 | Tem Investigations of CdTe/GaAs(001) Interfaces. Materials Research Society Symposia Proceedings, 1993, 319, 129. | 0.1 | 0 |
| 101 | Schottky barrier tunability in Al/ZnSe interfaces. Journal of Crystal Growth, 1998, 184-185, 193-198. | 1.5 | Ο |
| 102 | Evidence of bipolar charge transport in PTCDA. Solid State Communications, 2002, 123, 155-160. | 1.9 | 0 |
| 103 | Thermal diffusion of indium in perylenetetracarboxylic dianhydride. European Physical Journal Special Topics, 2006, 132, 127-132. | 0.2 | Ο |
| 104 | Organic Optoelectronics: Self-Suspended Nanomesh Scaffold for Ultrafast Flexible Photodetectors Based on Organic Semiconducting Crystals (Adv. Mater. 28/2018). Advanced Materials, 2018, 30, 1870204. | 21.0 | 0 |
| 105 | EXAFS Study of SnO2 Xerogel Doped with Sb and PTCDA. Physica Scripta, 2005, , 329. | 2.5 | 0 |
| 106 | Microscopic control of ZnSe–GaAs heterojunction band offsets. , 1993, , 557-565. | | 0 |